

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **BLX96** is Designed for Class A Television Band IV- V Amplifier Applications Requiring High Linearity.

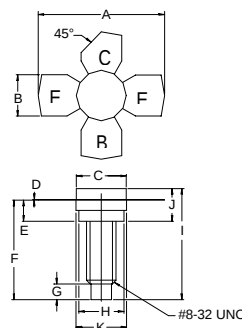
FEATURES:

- $P_G = 7.0$ dB Typical at 860 MHz
- $IMD_3 = -63$ dBc Typ. at $P_{REF} = 0.5$ W
- **Omnigold™** Metallization System

MAXIMUM RATINGS

I_C	1.0 A
V_{CB}	45 V
P_{DISS}	16 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	11 $^\circ C/W$

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

ORDER CODE: ASI10784

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 40$ mA	24			V
BV_{CER}	$I_C = 40$ mA $R_{BE} = 10 \Omega$	50			V
BV_{CBO}	$I_C = 2$ mA	45			V
BV_{EBO}	$I_E = 0.5$ mA	3.5			V
h_{FE}	$V_{CE} = 20$ V $I_C = 250$ mA	20		150	---
C_{OB}	$V_{CB} = 20$ V $f = 1.0$ MHz			10	pF
P_G	$V_{CE} = 25$ V $I_C = 250$ mA $P_{REF} = 0.5$ W	6.0	7.0		dB
IMD_3	$F = 860$ MHz Vision = -8.0 dB Sound = -7.0 dB Chroma = -16 dB			-60	dBc